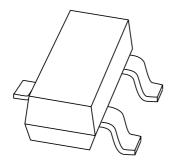
## DISCRETE SEMICONDUCTORS

## DATA SHEET



# **BAV170**Low-leakage double diode

Product data sheet Supersedes data of 1999 May 11 2003 Mar 25



## Low-leakage double diode

### **BAV170**

#### **FEATURES**

- Plastic SMD package
- Low leakage current: typ. 3 pA
- Switching time: typ. 0.8 μs
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

#### **APPLICATION**

 Low-leakage current applications in surface mounted circuits.

#### **MARKING**

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BAV170	JX*

#### Note

1. \* = p: Made in Hong Kong.

\* = t : Made in Malaysia.

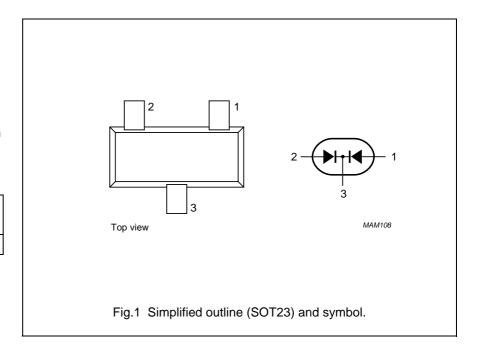
\* = W : Made in China.

#### **DESCRIPTION**

Epitaxial, medium-speed switching, double diode in a small SOT23 plastic SMD package. The diodes are in common cathode configuration.

#### **PINNING**

PIN	DESCRIPTION	
1	anode	
2	anode	
3	common cathode	



## Low-leakage double diode

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#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
$V_{RRM}$	repetitive peak reverse voltage		_	85	V
$V_R$	continuous reverse voltage		_	75	V
I <sub>F</sub>	continuous forward current	single diode loaded; note 1; see Fig.2	-	215	mA
		double diode loaded; note 1; see Fig.2	_	125	mA
I <sub>FRM</sub>	repetitive peak forward current		_	500	mA
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; T <sub>j</sub> = 25 °C prior to surge; see Fig.4			
		$t_p = 1 \mu s$	_	4	Α
		t <sub>p</sub> = 1 ms	_	1	Α
		t <sub>p</sub> = 1 s	_	0.5	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; note 1	_	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C

#### Note

#### **ELECTRICAL CHARACTERISTICS**

 $T_j = 25$  °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
Per diode					
V <sub>F</sub>	forward voltage	see Fig.3			
		I <sub>F</sub> = 1 mA	_	900	mV
		I <sub>F</sub> = 10 mA	_	1000	mV
		I <sub>F</sub> = 50 mA	_	1100	mV
		I <sub>F</sub> = 150 mA	_	1250	mV
I <sub>R</sub>	reverse current	see Fig.5			
		V <sub>R</sub> = 75 V	0.003	5	nA
		V <sub>R</sub> = 75 V; T <sub>j</sub> = 150 °C	3	80	nA
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 0; see Fig.6	2	_	pF
t <sub>rr</sub>	reverse recovery time	when switched from $I_F$ = 10 mA to $I_R$ = 10 mA; $R_L$ = 100 $\Omega$ ; measured at $I_R$ = 1 mA; see Fig.7	0.8	3	μS

<sup>1.</sup> Device mounted on a FR4 printed-circuit board.

## Low-leakage double diode

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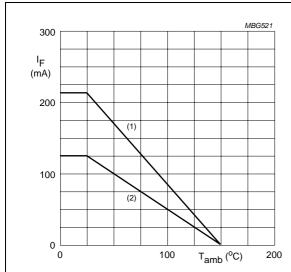
#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-tp</sub>	thermal resistance from junction to tie-point		360	K/W
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	500	K/W

#### Note

1. Device mounted on a FR4 printed-circuit board.

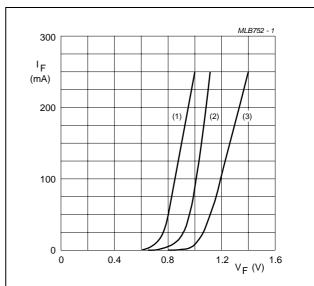
#### **GRAPHICAL DATA**



Device mounted on a FR4 printed-circuit board.

- (1) Single diode loaded.
- (2) Double diode loaded.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1)  $T_j = 150 \,^{\circ}\text{C}$ ; typical values.
- (2)  $T_j = 25$  °C; typical values.
- (3)  $T_j = 25$  °C; maximum values.

Fig.3 Forward current as a function of forward voltage; per diode.

## Low-leakage double diode

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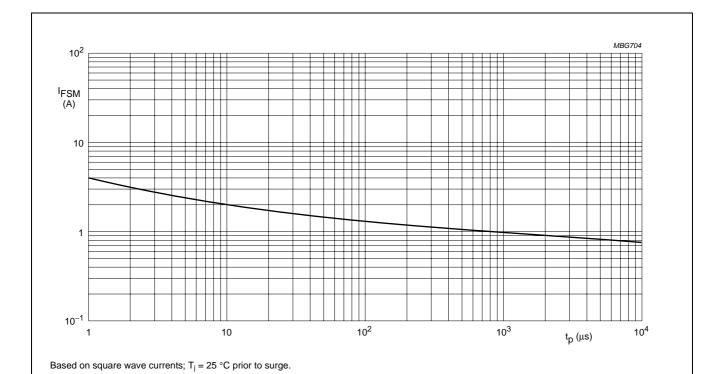
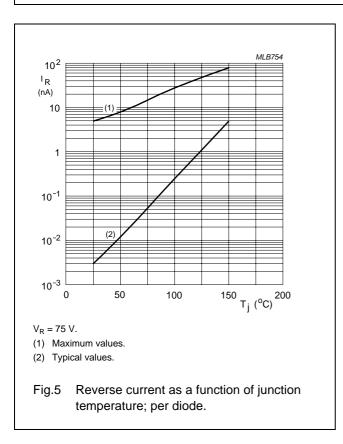
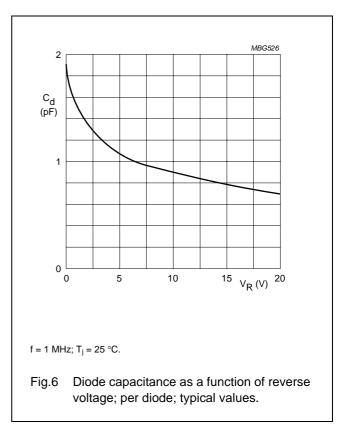


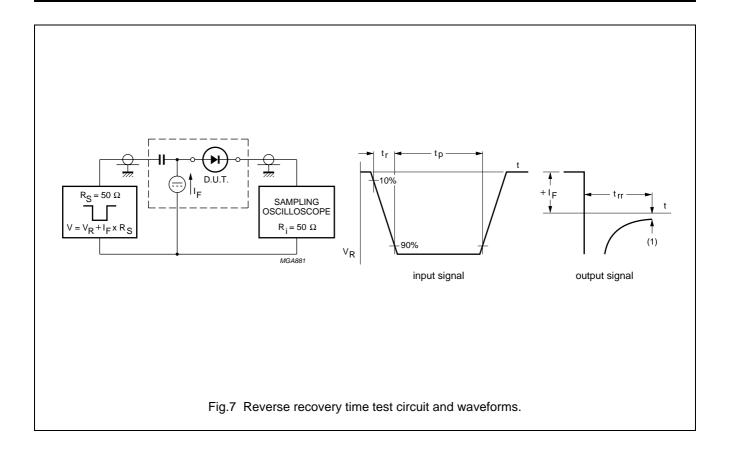
Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration per diode.





## Low-leakage double diode

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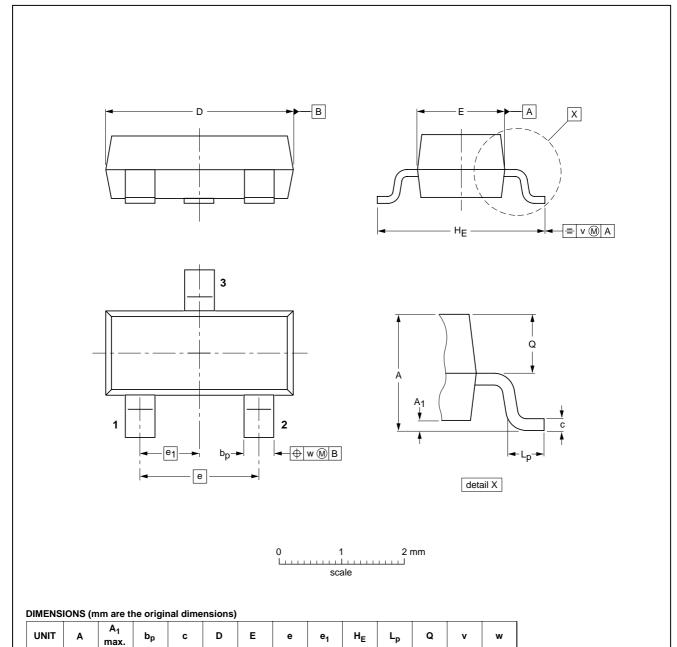
## Low-leakage double diode

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#### **PACKAGE OUTLINE**

Plastic surface mounted package; 3 leads

SOT23



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	1330E DATE
SOT23		TO-236AB				<del>-97-02-28-</del> 99-09-13

1.9

0.45

0.55

0.2

0.1

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0.48

0.38

0.15

## Low-leakage double diode

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#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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2003 Mar 25

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